





EC26 25 ET T TS -15.000M

Frequency Tolerance/Stability — ±25ppm Maximum

Operating Temperature Range -40°C to +85°C

Nominal Frequency

☐ Pin 1 Connection

Tri-State (High Impedance)

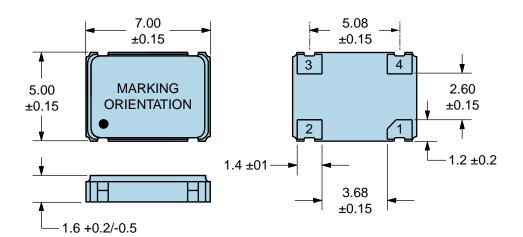
- Duty Cycle 50 ±5(%)

#25ppm Maximum (Inclusive of all conditions: Calibration Tolerance at 25°C, Frequency Stability over the Operating Temperature Range, Supply Voltage Change, Ouput Load Change, First Year Aging at 25°C, Shock, and Vibration)  Operating Temperature Range  -40°C to +85°C  Supply Voltage  3.3Vdc ±10%  Input Current  10mA Maximum  Output Voltage Logic High (Voh)  90% of Vdd Minimum (IOH=-8mA)  Output Voltage Logic Low (Vol)  Rise/Fall Time  5nSec Maximum (W/15pF Load), 7nSec Maximum (w/30pF Load) (Measured at 20% to 80% of waveform)  Duty Cycle  Load Drive Capability  30pF Maximum  Output Logic Type  CMOS  Pin 1 Connection  Tri-State (High Impedance)  Tri-State Input Voltage (Vih and Vil)  **Tri-State Input Voltage (Vih and Vil)  #*One Maximum (Disabled Output: High Impedance)  RMS Phase Jitter  10mSec Maximum  10mSec Maximum	ELECTRICAL SPECIFICATIONS		
Operating Temperature Range, Supply Voltage Change, Ouput Load Change, First Year Aging at 25°C, Shock, and Vibration)  Operating Temperature Range  -40°C to +85°C  Supply Voltage  3.3Vdc ±10%  Input Current  10mA Maximum  Output Voltage Logic High (Voh)  90% of Vdd Minimum (IOH=-8mA)  Output Voltage Logic Low (Vol)  10% of Vdd Maximum (IOL=+8mA)  Rise/Fall Time  5nSec Maximum (w/15pF Load), 7nSec Maximum (w/30pF Load) (Measured at 20% to 80% of waveform)  Duty Cycle  50 ±5(%) (Measured at 50% of waveform)  Load Drive Capability  30pF Maximum  Output Logic Type  CMOS  Pin 1 Connection  Tri-State (High Impedance)  +0.7Vdd Minimum or No Connect to Enable Output, +0.3Vdd Maximum to Disable Output (High Impedance)  Standby Current  10μA Maximum (Disabled Output: High Impedance)  RMS Phase Jitter  1pSec Maximum  10mSec Maximum  10mSec Maximum  10mSec Maximum	Nominal Frequency	15.000MHz	
Supply Voltage   3.3Vdc ±10%	Frequency Tolerance/Stability	Operating Temperature Range, Supply Voltage Change, Ouput Load Change, First Year Aging at 25°C,	
Input Current  10mA Maximum  Output Voltage Logic High (Voh) 90% of Vdd Minimum (IOH=-8mA)  Output Voltage Logic Low (Vol) 10% of Vdd Maximum (IOL=+8mA)  Rise/Fall Time 5nSec Maximum (w/15pF Load), 7nSec Maximum (w/30pF Load) (Measured at 20% to 80% of waveform)  Duty Cycle 50 ±5(%) (Measured at 50% of waveform)  Load Drive Capability 30pF Maximum  Output Logic Type CMOS  Pin 1 Connection Tri-State (High Impedance)  Tri-State Input Voltage (Vih and Vil) h-0.7Vdd Minimum or No Connect to Enable Output, +0.3Vdd Maximum to Disable Output (High Impedance)  Standby Current 10µA Maximum (Disabled Output: High Impedance)  RMS Phase Jitter 10mSec Maximum 10mSec Maximum	Operating Temperature Range	-40°C to +85°C	
Output Voltage Logic High (Voh)       90% of Vdd Minimum (IOH=-8mA)         Output Voltage Logic Low (Vol)       10% of Vdd Maximum (IOL=+8mA)         Rise/Fall Time       5nSec Maximum (w/15pF Load), 7nSec Maximum (w/30pF Load) (Measured at 20% to 80% of waveform)         Duty Cycle       50 ±5(%) (Measured at 50% of waveform)         Load Drive Capability       30pF Maximum         Output Logic Type       CMOS         Pin 1 Connection       Tri-State (High Impedance)         Tri-State Input Voltage (Vih and Vil)       +0.7Vdd Minimum or No Connect to Enable Output, +0.3Vdd Maximum to Disable Output (High Impedance)         Standby Current       10μA Maximum (Disabled Output: High Impedance)         RMS Phase Jitter       1pSec Maximum (12kHz to 20MHz offset frequency)         Start Up Time       10mSec Maximum	Supply Voltage	3.3Vdc ±10%	
Output Voltage Logic Low (Vol)       10% of Vdd Maximum (IOL=+8mA)         Rise/Fall Time       5nSec Maximum (w/15pF Load), 7nSec Maximum (w/30pF Load) (Measured at 20% to 80% of waveform)         Duty Cycle       50 ±5(%) (Measured at 50% of waveform)         Load Drive Capability       30pF Maximum         Output Logic Type       CMOS         Pin 1 Connection       Tri-State (High Impedance)         Tri-State Input Voltage (Vih and Vil)       +0.7Vdd Minimum or No Connect to Enable Output, +0.3Vdd Maximum to Disable Output (High Impedance)         Standby Current       10μA Maximum (Disabled Output: High Impedance)         RMS Phase Jitter       1pSec Maximum (12kHz to 20MHz offset frequency)         Start Up Time       10mSec Maximum	Input Current	10mA Maximum	
Rise/Fall Time  5nSec Maximum (w/15pF Load), 7nSec Maximum (w/30pF Load) (Measured at 20% to 80% of waveform)  50 ±5(%) (Measured at 50% of waveform)  Load Drive Capability  30pF Maximum  Output Logic Type  CMOS  Pin 1 Connection  Tri-State (High Impedance)  Tri-State Input Voltage (Vih and Vil)  +0.7Vdd Minimum or No Connect to Enable Output, +0.3Vdd Maximum to Disable Output (High Impedance)  Standby Current  10µA Maximum (Disabled Output: High Impedance)  RMS Phase Jitter  1pSec Maximum (12kHz to 20MHz offset frequency)  Start Up Time  10mSec Maximum	Output Voltage Logic High (Voh)	90% of Vdd Minimum (IOH=-8mA)	
Duty Cycle  50 ±5(%) (Measured at 50% of waveform)  Load Drive Capability  30pF Maximum  Output Logic Type  CMOS  Pin 1 Connection  Tri-State (High Impedance)  +0.7Vdd Minimum or No Connect to Enable Output, +0.3Vdd Maximum to Disable Output (High Impedance)  Standby Current  10µA Maximum (Disabled Output: High Impedance)  RMS Phase Jitter  1pSec Maximum (12kHz to 20MHz offset frequency)  Start Up Time  10mSec Maximum	Output Voltage Logic Low (Vol)	10% of Vdd Maximum (IOL=+8mA)	
Load Drive Capability       30pF Maximum         Output Logic Type       CMOS         Pin 1 Connection       Tri-State (High Impedance)         Tri-State Input Voltage (Vih and Vil)       +0.7Vdd Minimum or No Connect to Enable Output, +0.3Vdd Maximum to Disable Output (High Impedance)         Standby Current       10μA Maximum (Disabled Output: High Impedance)         RMS Phase Jitter       1pSec Maximum (12kHz to 20MHz offset frequency)         Start Up Time       10mSec Maximum	Rise/Fall Time	5nSec Maximum (w/15pF Load), 7nSec Maximum (w/30pF Load) (Measured at 20% to 80% of waveform)	
Output Logic Type CMOS Pin 1 Connection Tri-State (High Impedance)  Tri-State Input Voltage (Vih and Vil) +0.7Vdd Minimum or No Connect to Enable Output, +0.3Vdd Maximum to Disable Output (High Impedance)  Standby Current 10µA Maximum (Disabled Output: High Impedance)  RMS Phase Jitter 1pSec Maximum (12kHz to 20MHz offset frequency)  Start Up Time 10mSec Maximum	Duty Cycle	50 ±5(%) (Measured at 50% of waveform)	
Pin 1 Connection       Tri-State (High Impedance)         Tri-State Input Voltage (Vih and Vil)       +0.7Vdd Minimum or No Connect to Enable Output, +0.3Vdd Maximum to Disable Output (High Impedance)         Standby Current       10μA Maximum (Disabled Output: High Impedance)         RMS Phase Jitter       1pSec Maximum (12kHz to 20MHz offset frequency)         Start Up Time       10mSec Maximum	Load Drive Capability	30pF Maximum	
Tri-State Input Voltage (Vih and Vil) +0.7Vdd Minimum or No Connect to Enable Output, +0.3Vdd Maximum to Disable Output (High Impedance)  Standby Current 10μΑ Maximum (Disabled Output: High Impedance)  RMS Phase Jitter 1pSec Maximum (12kHz to 20MHz offset frequency)  Start Up Time 10mSec Maximum	Output Logic Type	CMOS	
Impedance)  Standby Current 10µA Maximum (Disabled Output: High Impedance)  RMS Phase Jitter 1pSec Maximum (12kHz to 20MHz offset frequency)  Start Up Time 10mSec Maximum	Pin 1 Connection	Tri-State (High Impedance)	
RMS Phase Jitter 1pSec Maximum (12kHz to 20MHz offset frequency)  Start Up Time 10mSec Maximum	Tri-State Input Voltage (Vih and Vil)	1 /	
Start Up Time 10mSec Maximum	Standby Current	10μA Maximum (Disabled Output: High Impedance)	
·	RMS Phase Jitter	1pSec Maximum (12kHz to 20MHz offset frequency)	
Storage Temperature Range -55°C to +125°C	Start Up Time	10mSec Maximum	
	Storage Temperature Range	-55°C to +125°C	

ENVIRONMENTAL & MECHANICAL SPECIFICATIONS		
ESD Susceptibility	MIL-STD-883, Method 3015, Class 1, HBM: 1500V	
Fine Leak Test	MIL-STD-883, Method 1014, Condition A	
Flammability	UL94-V0	
Gross Leak Test	MIL-STD-883, Method 1014, Condition C	
Mechanical Shock	MIL-STD-883, Method 2002, Condition B	
Moisture Resistance	MIL-STD-883, Method 1004	
Moisture Sensitivity	J-STD-020, MSL 1	
Resistance to Soldering Heat	MIL-STD-202, Method 210, Condition K	
Resistance to Solvents	MIL-STD-202, Method 215	
Solderability	MIL-STD-883, Method 2003	
Temperature Cycling	MIL-STD-883, Method 1010, Condition B	
Vibration	MIL-STD-883, Method 2007, Condition A	



### **MECHANICAL DIMENSIONS (all dimensions in millimeters)**

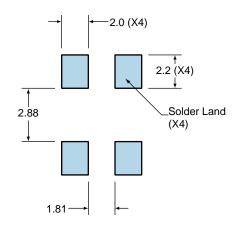


PIN	CONNECTION
1	Tri-State
2	Ground/Case Ground
3	Output
4	Supply Voltage

LINE	MARKING
1	ECLIPTEK
2	15.000M
3	XXYZZ XX=Ecliptek Manufacturing Code Y=Last Digit of the Year ZZ=Week of the Year

#### **Suggested Solder Pad Layout**

All Dimensions in Millimeters



All Tolerances are ±0.1



#### **OUTPUT WAVEFORM & TIMING DIAGRAM**



#### **Test Circuit for CMOS Output**



- Note 1: An external  $0.1\mu F$  low frequency tantalum bypass capacitor in parallel with a  $0.01\mu F$  high frequency ceramic bypass capacitor close to the package ground and  $V_{DD}$  pin is required.
- Note 2: A low capacitance (<12pF), 10X attenuation factor, high impedance (>10Mohms), and high bandwidth (>300MHz) passive probe is recommended.
- Note 3: Capacitance value  $\dot{C}_L$  includes sum of all probe and fixture capacitance.



## **Recommended Solder Reflow Methods**

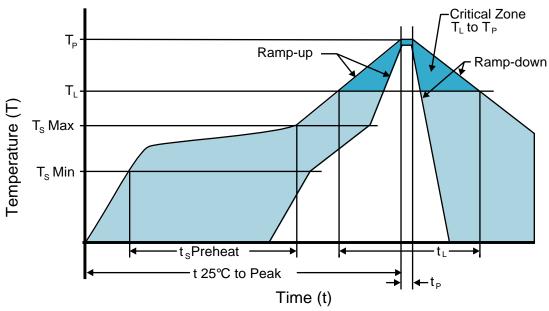


### **High Temperature Infrared/Convection**

3°C/second Maximum
150°C
175°C
200°C
60 - 180 Seconds
3°C/second Maximum
217°C
60 - 150 Seconds
260°C Maximum for 10 Seconds Maximum
250°C +0/-5°C
20 - 40 seconds
6°C/second Maximum
8 minutes Maximum
Level 1
Temperatures shown are applied to body of device.



### **Recommended Solder Reflow Methods**



#### Low Temperature Infrared/Convection 240°C

T <sub>S</sub> MAX to T <sub>L</sub> (Ramp-up Rate)	5°C/second Maximum
Preheat	
- Temperature Minimum (T <sub>s</sub> MIN)	N/A
- Temperature Typical (T <sub>S</sub> TYP)	150°C
- Temperature Maximum (T <sub>s</sub> MAX)	N/A
- Time (t <sub>s</sub> MIN)	60 - 120 Seconds
Ramp-up Rate (T <sub>L</sub> to T <sub>P</sub> )	5°C/second Maximum
Time Maintained Above:	
- Temperature (T∟)	150°C
- Time (t∟)	200 Seconds Maximum
Peak Temperature (T <sub>P</sub> )	240°C Maximum
Target Peak Temperature (T <sub>P</sub> Target)	240°C Maximum 1 Time / 230°C Maximum 2 Times
Time within 5°C of actual peak (tp)	10 seconds Maximum 2 Times / 80 seconds Maximum 1 Time
Ramp-down Rate	5°C/second Maximum
Time 25°C to Peak Temperature (t)	N/A
Moisture Sensitivity Level	Level 1
Additional Notes	Temperatures shown are applied to body of device.

#### **Low Temperature Manual Soldering**

185°C Maximum for 10 seconds Maximum, 2 times Maximum. (Temperatures shown are applied to body of device.)

### **High Temperature Manual Soldering**

260°C Maximum for 5 seconds Maximum, 2 times Maximum. (Temperatures shown are applied to body of device.)